

**NPN TRANSISTOR****8050****1.5A**

- Power Dissipation  
Pcm : 1.0W
- Collector Current  
Icm : 1.5A
- Collector-Base Voltage  
Vcbo: 45V

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS ( Ta=25 )**

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITION
Collector-Emitter Breakdown Voltage	BVceo	25			V	Ic=0.1mA
Collector-Base Breakdown Voltage	BVcbo	45			V	Ic=100μA
Emitter-Base Breakdown Voltage	BVebo	5			V	Ie=100 μ A
Collector-Base Leakage	Icbo			0.1	μA	Vcb=40V
Collector-Emitter Leakage	Iceo			0.1	μA	Vce=20V
Emitter-Base Leakage	Iebo			0.1	μA	Veb=5V
Collector-Emitter Saturation Voltage	Vce(sat )			0.6	V	Ic=1500mA, Ib=50mA
Base-Emitter Saturation Voltage	Vbe(sat)			1.2	V	Ic=1500mA, Ib=50mA
DC Current Gain	Hfe1 Hfe2	85 50		300		Vce=1V, Ic=50mA Vce=1V, Ic=500mA
Collector Current	Ic			1.5	A	
Peak Collector Current	Icp			8	A(Pulse)	
Current Gain Bandwidth	fT	150			MHz	Vcb=6V, Ic=20mA
Output Capacitance	Cob			32	pF	Vcb=20V, Ie=0, f=1MHz
Power Dissipation	Pc			1.0	W	
Junction Temperature	Tj			150		
Storage Temperature	Tstg	-55		150		

**Hfe1 Classification**

Rank	B	C	D
Range	85-160	120-200	160-300

**STANSON TECHNOLOGY**

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